

# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

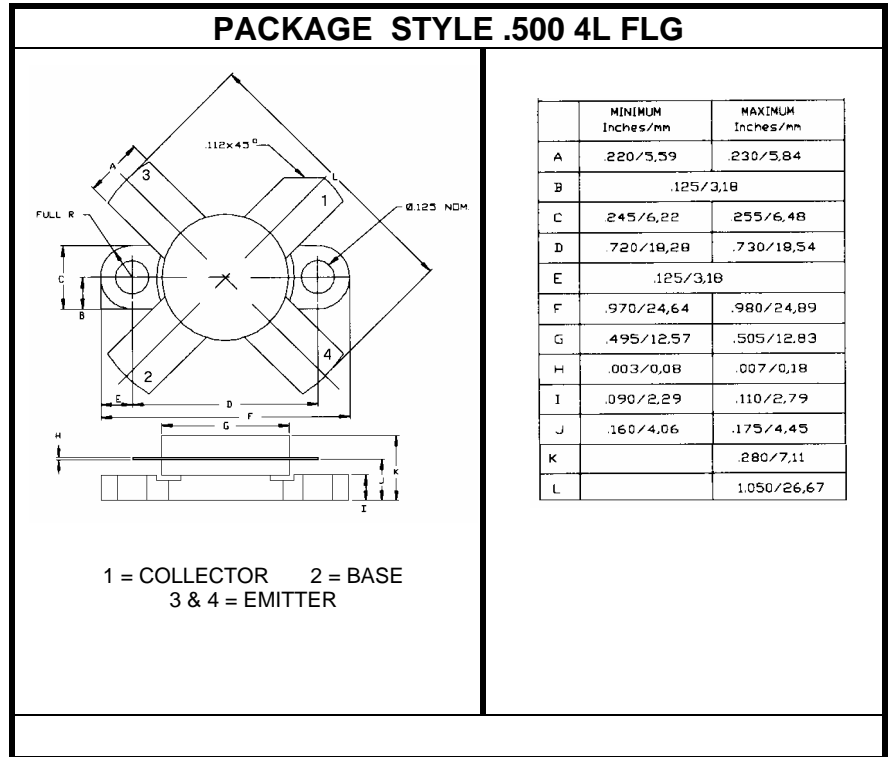
The **ASI BLW77** is Designed for use in class-AB or class-B operated high power transmitters in the H.F. and V.H.F bands and, as a Linear amplifier in the H.F. band.

## FEATURES:

- $P_G = 12$  dB min. at 15-30 W/1.6-28 MHz
- Common Emitter
- **Omnigold™** Metalization System

## MAXIMUM RATINGS

|               |                       |
|---------------|-----------------------|
| $I_C$         | 12 A                  |
| $V_{CB}$      | 70 V                  |
| $V_{CE}$      | 35 V                  |
| $P_{DISS}$    | 245 W @ $T_C = 25$ °C |
| $T_J$         | -65 °C to +200 °C     |
| $T_{STG}$     | -65 °C to +150 °C     |
| $\theta_{JC}$ | 0.71 °C/W             |



## CHARACTERISTICS $T_C = 25$ °C

| SYMBOL     | TEST CONDITIONS  | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|------------|--|---------|---------|---------|-------|
| $BV_{CEO}$ | $I_C = 100$ mA   | 35      |         |         | V     |
| $BV_{CES}$ | $I_C = 50$ mA  | 70      |         |         | V     |
| $BV_{EBO}$ | $I_E = 20$ mA  | 3.0     |         |         | V     |
| $I_{CES}$  | $V_E = 35$ V   |         |         | 20      | mA    |
| $h_{FE}$   | $V_{CE} = 5.0$ V $I_C = 7.0$ A   | 15      |         | 80      | ---   |
| $C_c$      | $V_{CB} = 28$ V $f = 1.0$ MHz  |         | 225     |         | pF    |
| $G_p$      | $V_{CE} = 28$ V $I_{C(ZS)} = 0.1$ A $f = 1.6-28$ MHz<br>$P_L = 15-130$ W (PEP) | 12      |         |         | dB    |
| $d_3$      |  |         |         | -30     | dB    |
| $\eta$     |  | 37.5    |         |         | %     |